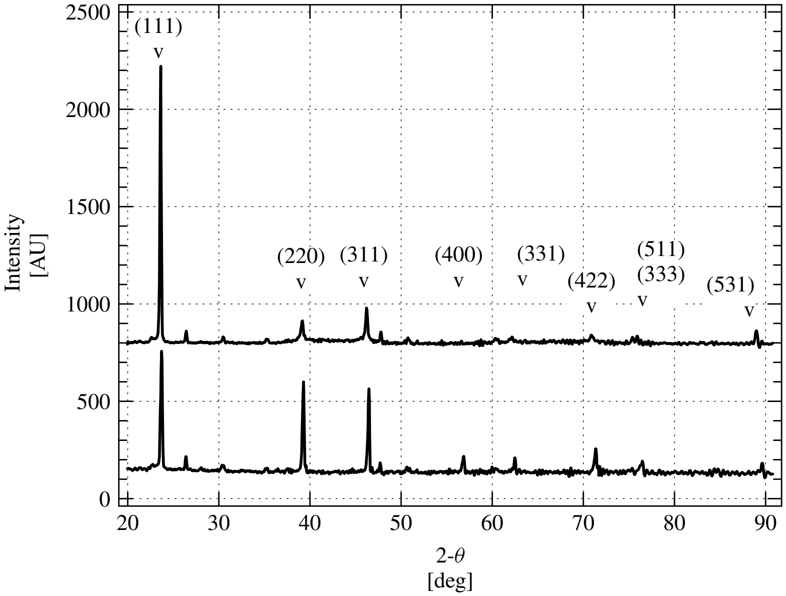

Figure 14.10 X-ray diffraction patterns of PVD CdTe/CdS thin-film structures before and after vapor $CdCl_2$ heat treatment at 420°C for 20 min, showing randomization of the film orientation. The primary peaks are due to the 1.5-μm-thick CdTe layer; the other peaks are due to the underlying CdS and ITO films

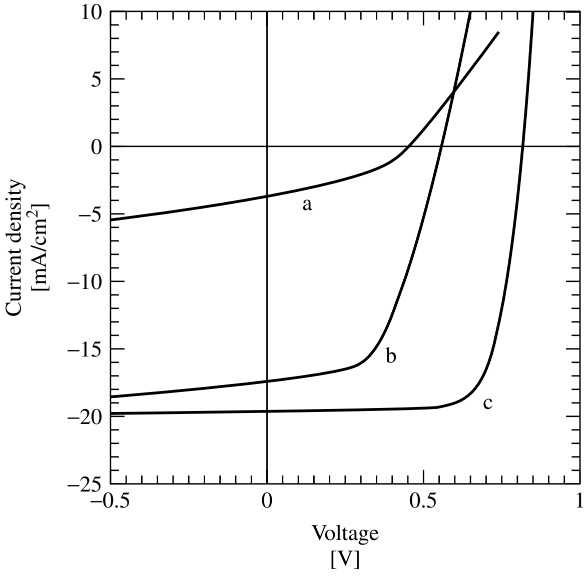

Figure 14.11 Light AM1.5 $J-V$ curves of PVD devices with Cu_2Te/C contacts and different post-deposition processing: (a) no heat treatment; (b) treatment at 550°C for 5 min in air; (c) treatment in $CdCl_2$ vapor at 420°C for 20 min in air [105]